KRC281M~KRC286M

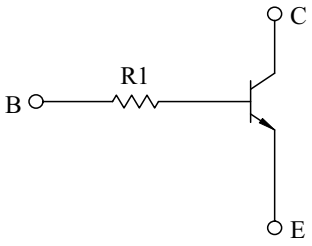
EPITAXIAL PLANAR NPN TRANSISTOR

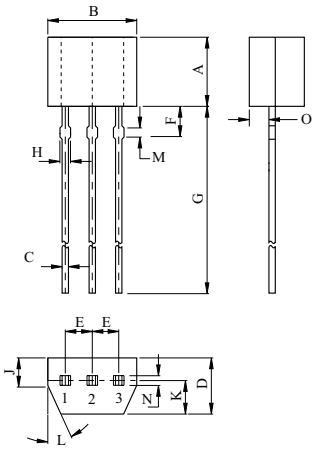
SWITCHING APPLICATION.
AUDIO MUTING APPLICATION.

FEATURES

- High emitter-base voltage : V_{EBO}=25V(Min)
- High reverse h_{FE} : reverse h_{FE}=150(Typ.) (V_{CE}=-2V, I_C=-4mA)
- Low on resistance : R_{on}=1Ω(Typ.) (I_B=5mA)
- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT





DIM	MILLIMETERS
A	3.20 MAX
B	4.30 MAX
C	0.55 MAX
D	2.40±0.15
E	1.27
F	2.30
G	14.00±0.50
H	0.60 MAX
J	1.05
K	1.45
L	25°
M	0.80
N	0.55 MAX
O	0.75

1. EMITTER
2. COLLECTOR
3. BASE

TO-92M

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	20	V
Emitter-Base Voltage	V_{EBO}	25	V
Collector Current	I_C	300	mA
Collector Power Dissipation	P_C	400	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage		BV_{CEO}	I_C=1mA	20	-	-	V
Collector-Base Breakdown Voltage		BV_{CBO}	I_C=50μA	50	-	-	V
Emitter-Base Breakdown Voltage		BV_{EBO}	I_E=50μA	25	-	-	V
Collector Cut-off Current		I_{CBO}	V_{CB}=50V, I_E=0	-	-	0.1	μA
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=30mA, I_B=3mA	-	-	0.1	V
DC Current Gain		h_{FE}	V_{CE}=2V, I_C=4mA	350	-	1200	
Input Resistor	KRC281M	R_1		-	2.2	-	k Ω
	KRC282M			-	4.7	-	
	KRC283M			-	5.6	-	
	KRC284M			-	6.8	-	
	KRC285M			-	10	-	
	KRC286M			-	22	-	
Transition Frequency		f_T *	V_{CE}=6V, I_C=4mA,	-	30	-	MHz
Collector Output Capacitance		C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	4.8	-	pF

* Characteristic of Transistor Only.

Note) h_{FE} Classification B:350 ~ 1200